



# STW18NB40 STH18NB40FI

## N-CHANNEL 400V - 0.19Ω - 18.4A TO-247/ISOWATT218 PowerMESH™ MOSFET

### PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STW18NB40	400 V	< 0.26 Ω	18.4 A
STH18NB40FI	400 V	< 0.26 Ω	12.4A

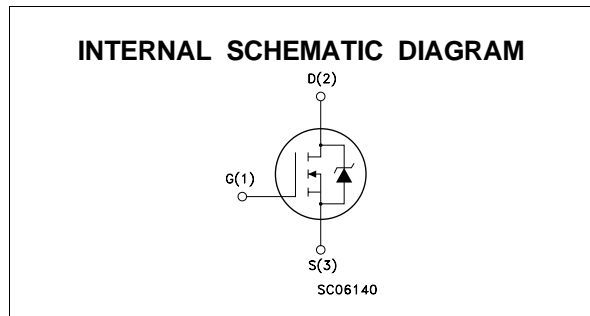
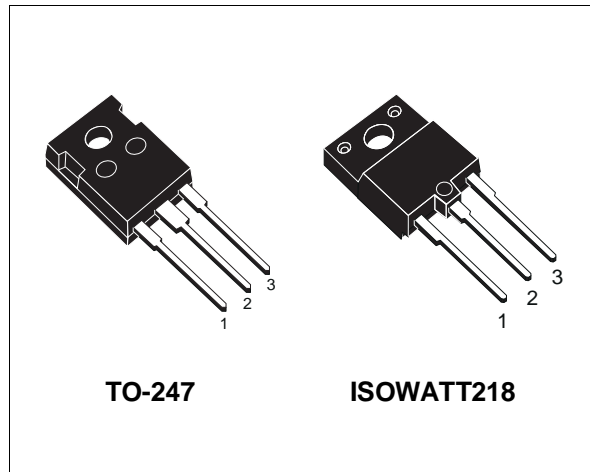
- TYPICAL R<sub>DS(on)</sub> = 0.19 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

### DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest RDS(on) per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW18NB40	STH18NB40FI	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	400		V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	400		V
V <sub>GS</sub>	Gate-source Voltage	± 30		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	18.4	12.4	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	11.6	7.8	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	73.6	73.6	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	190	80	W
	Derating Factor	1.52	0.64	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	4.5	4.5	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 18.4 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

## STW18NB40-STH18NB40FI

### THERMAL DATA

			TO-247	ISOWATT218	
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	0.66	1.56	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	30		°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ	0.1		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300		°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	18.4	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	400	mJ

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	400			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>c</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 30 V			± 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	3	4	5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 9.2 A		0.19	0.26	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	18.4			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 9.2 A	6.8	9.3		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		2480	3230	pF
C <sub>oss</sub>	Output Capacitance			435	570	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			47	66	pF

**ELECTRICAL CHARACTERISTICS** (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 200\text{ V}$ $I_D = 9.2\text{ A}$		27	35	ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		14	20	ns
$Q_g$	Total Gate Charge	$V_{DD} = 320\text{ V}$ $I_D = 18.4\text{ A}$ $V_{GS} = 10\text{ V}$		60	84	nC
$Q_{gs}$	Gate-Source Charge			16		nC
$Q_{gd}$	Gate-Drain Charge			28.3		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 320\text{ V}$ $I_D = 18.4\text{ A}$		13	18	ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		15	21	ns
$t_c$	Cross-over Time			27	35	ns

SOURCE DRAIN DIODE

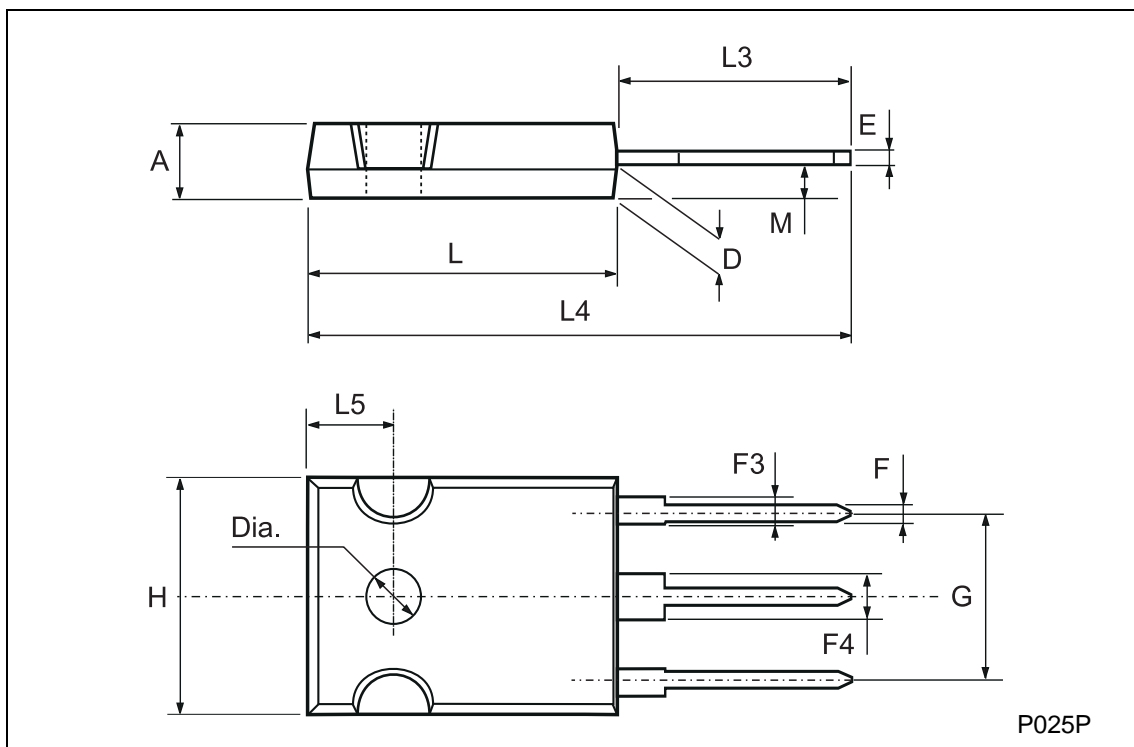
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				18.4	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				73.6	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 18.4\text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 18.4\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		480		ns
$Q_{rr}$	Reverse Recovery Charge			5.5		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			23		A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

( $\bullet$ ) Pulse width limited by safe operating area

**TO-247 MECHANICAL DATA**

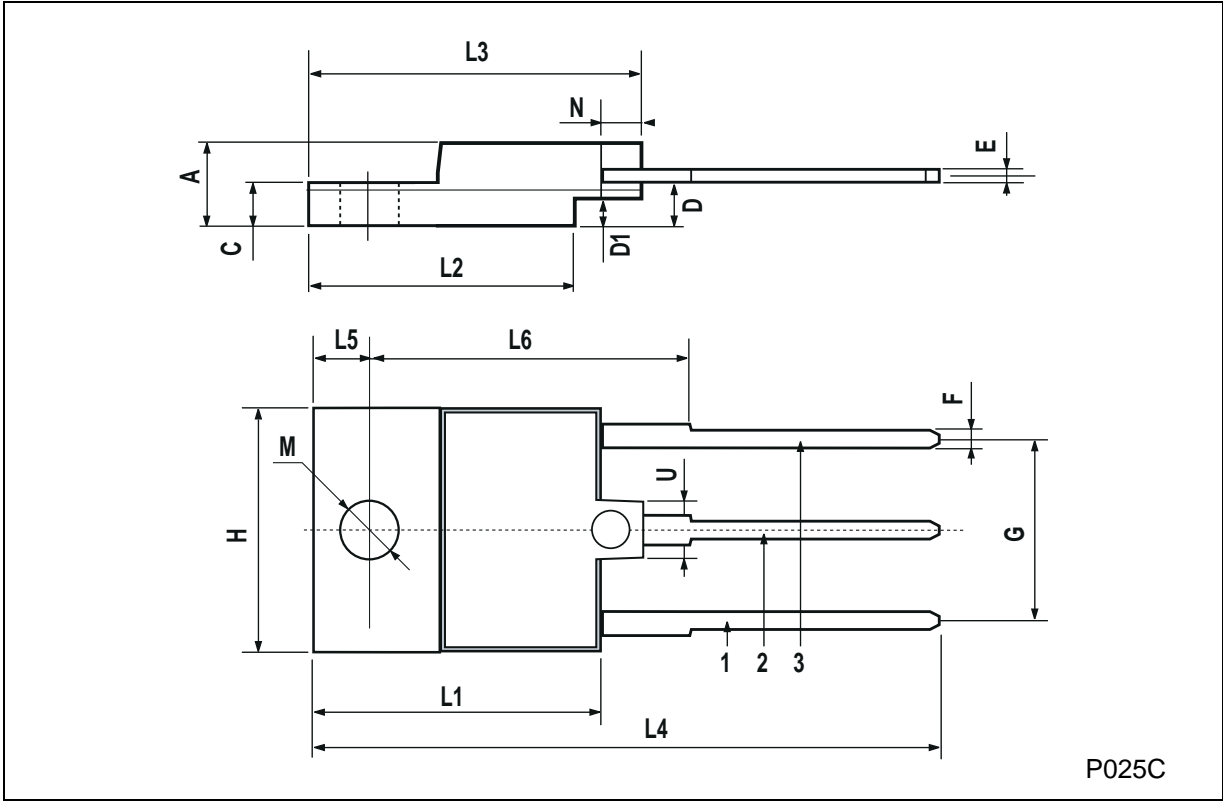
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559	0.413	0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118
Dia	3.55		3.65	0.140		0.144



P025P

**ISOWATT218 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.75		1	0.029		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	



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